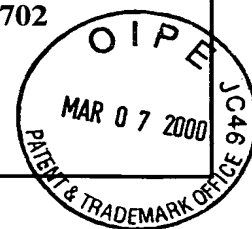


Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. ALSCP003	Application No.: 09/375,702
	Applicant: Perumal Ratnam Filing Date August 16, 1999	Group 2812



U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
<i>MA</i>	A1	5,120,671	6/9/92	Tang, <i>et al.</i>	437	43	11/29/90
<i>MA</i>	A2	5,470,773	11/28/95	Liu, <i>et al.</i>	437	43	4/25/94

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>MA</i>	C1	Chang, <i>et al.</i> , "Corner-Field Induced Drain Leakage In Thin Oxide MOSFETs," <i>IEDM Technical Digest</i> , 31.2, pp. 714-17 (1987).
	C2	Kume, <i>et al.</i> , "A Flash-Erase EEPROM Cell With An Asymmetric Source and Drain Structure," <i>IEDM Technical Digest</i> , 25.8, pp. 560-63 (1987).
	C3	Yokozawa, <i>et al.</i> , "Low-Field-Stress Erasing Scheme for Highly-Reliable Flash Memories," NEC ULSI Device Development Laboratories, 24 pages, February 12, 1997.
Examiner	Date Considered	
<i>MA</i>	<i>5-16</i>	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.